



60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V(BR)DSS	R _{DS(on)} Max	I _D Max T _A = +25°C (Note 6)
-60V	$125m\Omega @ V_{GS} = -10V$	-3.0 A
-60 V	190mΩ @ V_{GS} = -4.5V	-2.4 A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- **DC-DC Converters**
- **Power Management Functions**
- **Disconnect Switches**
- Motor Control

Features and Benefits

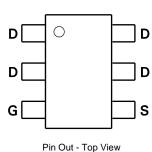
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

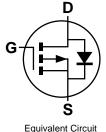
Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Weight: 0.018 grams (Approximate)



Top View





Ordering Information (Note 4)

	Part Number	Compliance	Case	Quantity per reel				
	ZXMP6A17E6TA	Standard	SOT-26	3,000				
Note:	ote: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.							

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



6A17 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Kev

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	Е	F	G	Н	Ι	J	K	L	М	Ν

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

(Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-60	V
Gate-Source Voltage			V _{GS}	±20	V
		(Note 6)		-3	
Continuous Drain Current	$V_{GS} = -10V$	$T_{A} = +70^{\circ}C$ (Note 6)	ID	-2.4	А
		(Note 5)		-2.3	
Pulsed Drain Current	$V_{GS} = -10V$	(Note 7)	I _{DM}	-13.6	А
Continuous Source Current (Body Diode) (Note 6)		(Note 6)	ls	-2.5	A
Pulsed Source Current (Body Diode) (Note 7)		(Note 7)	I _{SM}	-13.6	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

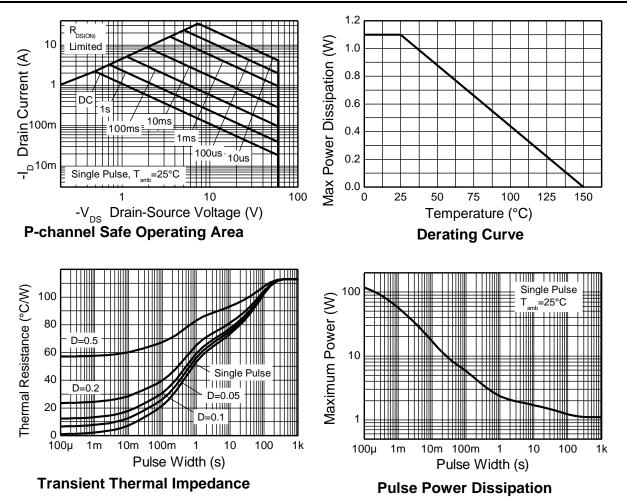
Characteristic	Characteristic			Unit
Power Dissipation	(Note 5)		1.1 8.8	W
Linear Derating Factor	(Note 6)	PD PD	1.92 15.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 5) (Note 6)		113 65	°C/W
Operating and Storage Temperature Range		TJ, T _{STG}	-55 to +150	°C

Notes: 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Same as Note 5, except the device is measured at t \leq 5 sec.

7. Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.

Thermal Characteristics





Notes:

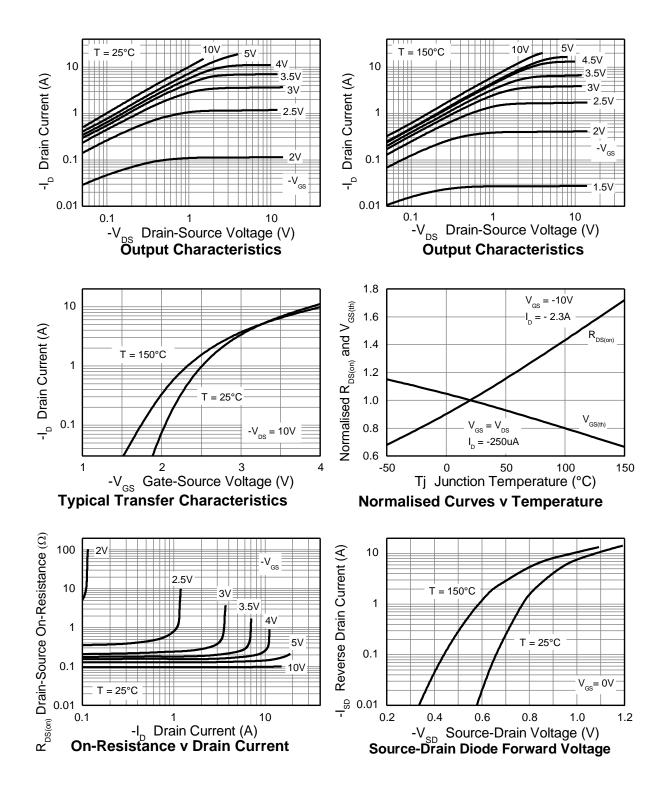
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition	
OFF CHARACTERISTICS	- 		- 71-					
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_		V	$I_D = -250 \mu A, V_{GS} = 0 V$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	$V_{DS} = -60V, V_{GS} = 0V$		
Gate-Source Leakage	Igss		—	±100	nA	$V_{GS} = \pm 20V, V_{E}$		
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(th)}	-1	_	-3	V	$I_D = -250 \mu A, V_D$	$_{\rm S} = V_{\rm GS}$	
Static Drain-Source On-Resistance (Note 8)			0.100	0.125	Ω	V _{GS} = -10V, I _D = -2.3A		
Static Dialit-Source Off-Resistance (Note 8)	R _{DS} (ON)	_	0.130	0.190	12	V _{GS} = -4.5V, I _D = -1.9A		
Forward Transconductance (Notes 8 & 9)	g fs	_	4.7	_	S	$V_{DS} = -15V, I_{D}$	= -2.3A	
Diode Forward Voltage (Note 8)	V _{SD}	_	-0.85	-0.95	V	$I_{S} = -2A, V_{GS} = 0V$		
Reverse Recovery Time (Note 9)	t _{rr}		25.1		ns	I _F = -1.7A, di/dt = 100A/μs		
Reverse Recovery Charge (Note 9)	Qrr	_	27.2	_	nC			
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	Ciss	—	637	—	pF	V 20V/V	0)/	
Output Capacitance	Coss	—	70		pF	− V _{DS} = -30V, V _G − f = 1MHz	s = 0V	
Reverse Transfer Capacitance	C _{rss}	_	53	_	pF	1 = 110112		
Total Gate Charge (Note 10)	Qg	_	9.8	_	nC	$V_{GS} = -5V$		
Total Gate Charge (Note 10)	Qg	_	17.7	_	nC		$V_{DS} = -30V$	
Gate-Source Charge (Note 10)	Q _{gs}	_	1.6	_	nC	$V_{GS} = -10V$	$I_{D} = -2.3A$	
Gate-Drain Charge (Note 10)	Q _{gd}	_	4.4	_	nC			
Turn-On Delay Time (Note 10)	t _{D(on)}		2.6		ns		•	
Turn-On Rise Time (Note 10)	tr		3.4	_	ns	$V_{DD} = -30V, V_{G}$	s = -10V	
Turn-Off Delay Time (Note 10)	t _{D(off)}	_	26.2	—	ns	I _D = -1A, R _G ≅ 6		
Turn-Off Fall Time (Note 10)	tf	_	11.3		ns			

Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
For design aid only, not subject to production testing.
Switching characteristics are independent of operating junction temperatures.

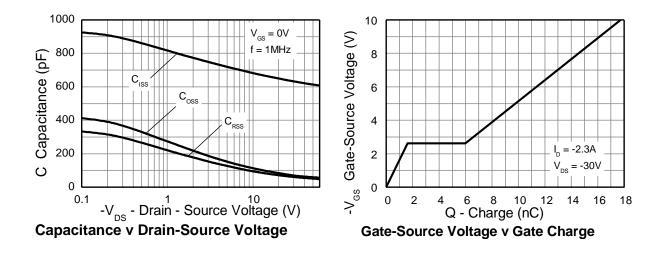


Typical Characteristics

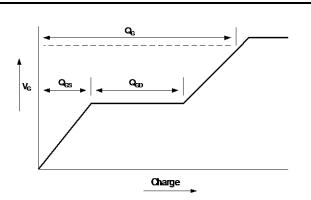




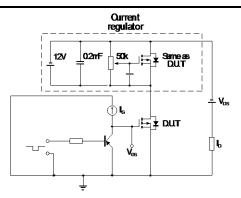
Typical Characteristics (cont.)



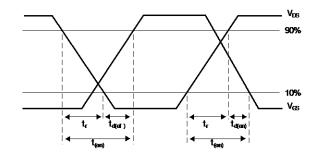
Test Circuits



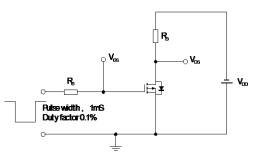
Basic gate charge waveform



Gate charge test circuit





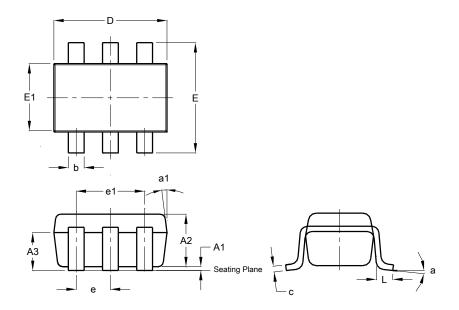


Switching time test circuit



Package Outline Dimensions

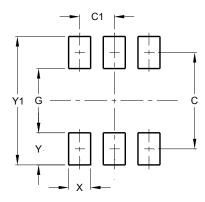
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SC	DT26	
Dim	Min	Max	Тур
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
Ċ	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
ш	2.70	3.00	2.80
E1	1.50	1.70	1.60
1	0.35	0.55	0.40
а	-	-	8°
a1	-	-	7°
All	Dimen	sions	in mm

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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